

ABSTRACT OF THE DISCLOSURE

An conductive coating serves as a light shield film and is kept at a give voltage. A metal interconnection is located in the same layer as a source line and connected to the drain of a thin-film transistor. An interlayer insulating film is constituted of at least lower and upper insulating layers and formed between the conductive coating and the source line. According to one aspect of the invention, an auxiliary capacitor is formed by the metal interconnection and the conductive coating serving as both electrodes and at least the lower insulating layer film serving as a dielectric. The auxiliary capacitor is formed in a region of the interlayer insulating film in which the upper insulating layer has been removed by etching. According to another aspect of the invention, the conductive coating has a portion that is in contact with the lower insulating layer in a region where the conductive coating coextends with the metal interconnection.